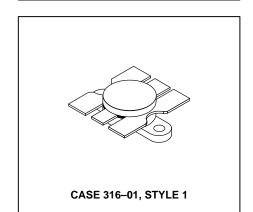
# The RF Line NPN Silicon RF Power Transistor

... designed for 12.5 Volt UHF large—signal amplifier applications in industrial and commercial FM equipment operating to 512 MHz.

- Specified 12.5 Volt, 470 MHz Characteristics —
   Output Power = 15 Watts
   Minimum Gain = 7.8 dB
   Efficiency = 55%
- Characterized with Series Equivalent Large-Signal Impedance Parameters
- Built-In Matching Network for Broadband Operation
- Tested for Load Mismatch Stress at all Phase Angles with 20:1 VSWR @ 16–Volt High Line and Overdrive
- Circuit board photomaster available upon request by contacting RF Tactical Marketing in Phoenix, AZ.

# **MRF641**

15 W, 470 MHz CONTROLLED Q RF POWER TRANSISTOR NPN SILICON



### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	VCEO	16	Vdc
Collector–Base Voltage	V <sub>СВО</sub>	36	Vdc
Emitter-Base Voltage	VEBO	4.0	Vdc
Collector Current — Continuous	IC	3.0	Adc
Total Device Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	PD	43.7 0.25	Watts W/°C
Storage Temperature Range	T <sub>stg</sub>	-65 to +150	°C

## THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	4.0	°C/W

# **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = 25°C unless otherwise noted.)

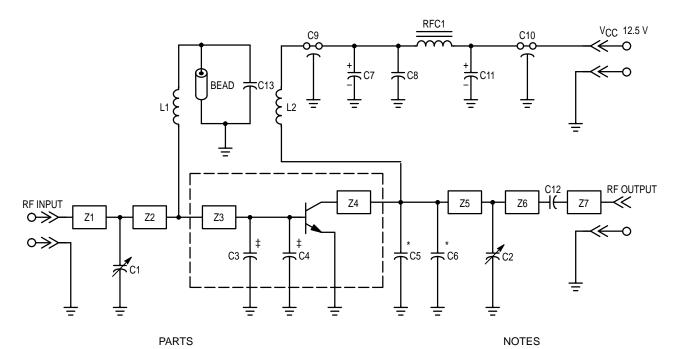
Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage (I <sub>C</sub> = 20 mAdc, I <sub>B</sub> = 0)	V(BR)CEO	16	_	_	Vdc
Collector–Emitter Breakdown Voltage (I <sub>C</sub> = 20 mAdc, V <sub>BE</sub> = 0)	V(BR)CES	36	_	_	Vdc
Emitter–Base Breakdown Voltage (I <sub>E</sub> = 5.0 mAdc, I <sub>C</sub> = 0)	V(BR)EBO	4.0	_	_	Vdc
Collector Cutoff Current (VCE = 15 Vdc, VBE = 0, TC = 25°C)	ICES	_	_	5.0	mAdc

(continued)



# **ELECTRICAL CHARACTERISTICS** — **continued** $(T_C = 25^{\circ}C)$ unless otherwise noted.)

Characteristic	Symbol	Min	Тур	Max	Unit
ON CHARACTERISTICS					
DC Current Gain (I <sub>C</sub> = 1.0 Adc, V <sub>CE</sub> = 5.0 Vdc)	hFE	30	70	150	_
DYNAMIC CHARACTERISTICS					
Output Capacitance (V <sub>CB</sub> = 12.5 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz)	C <sub>ob</sub>	_	40	60	pF
FUNCTIONAL TESTS					
Common–Emitter Amplifier Power Gain (V <sub>CC</sub> = 12.5 Vdc, P <sub>Out</sub> = 15 W, f = 470 MHz)	G <sub>pe</sub>	7.8	8.5	_	dB
Collector Efficiency (V <sub>CC</sub> = 12.5 Vdc, P <sub>Out</sub> = 15 W, f = 470 MHz)	η	55	60	_	%
Output Mismatch Stress (V <sub>CC</sub> = 16 Vdc, P <sub>in</sub> = 3.0 W, f = 470 MHz, VSWR = 20:1, All Phase Angles)	Ψ	No Degradation in Output Power			



Z1 — 1.225" x 0.187" Microstrip Z2 — 0.884" x 0.187" Microstrip

Z3 — Capacitor Block (Base)

Z4 — Collector Block

Z5 — 1.1" x 0.187" Microstrip

Z6 — 0.433" x 0.187" Microstrip

Z7 — 0.4" x 0.187" Microstrip

Dotted Area — Capacitor Assembly

C1, C2 — 0.8-10 pF Johanson

C3, C4 — 24 pF Chip Caps 100 mils ATC

C5, C6 — 22 pF Chip Caps 100 mils ATC

C12 — 220 pF Chip Cap 100 mils ATC

C7, C11 — 1.0  $\mu F$  Tantalum 35 Vdc

C9, C10 — 680 pF Feedthrough Allen-Bradley

C13 — 200 pF UNELCO

 $C8 - 0.1 \mu F$ , 50 V Erie Red Cap

RFC1 — VK 200 — 104B Ferrite Choke

L1 — 4 Turns 0.2" Dia. #16 AWG

L2 - 9 Turns 0.15" Dia. #16 AWG

Bead — Ferroxcube 56-590-65-35EB

\*C5, C6, are mounted as close to the capacitor assembly as possible.

‡‡C3, C4 are mounted in the capacitor assembly. Board — 62.5 mil Glass Teflon,  $\epsilon_{\Gamma}$  = 2.55.

**Figure 1. Test Circuit Schematic** 

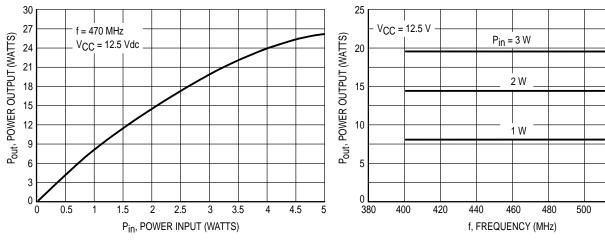


Figure 2. Power Output versus Power Input

Figure 3. Power Output versus Frequency

520

540

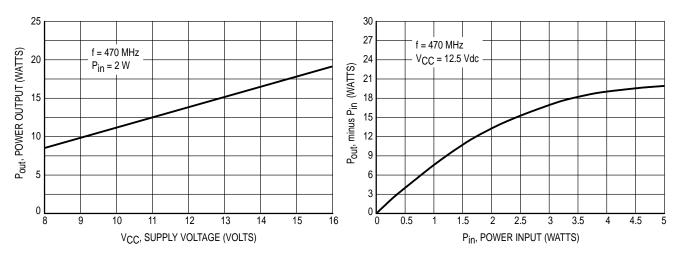
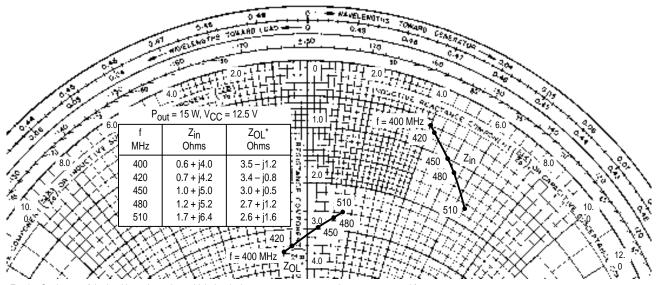


Figure 4. Power Output versus Supply Voltage

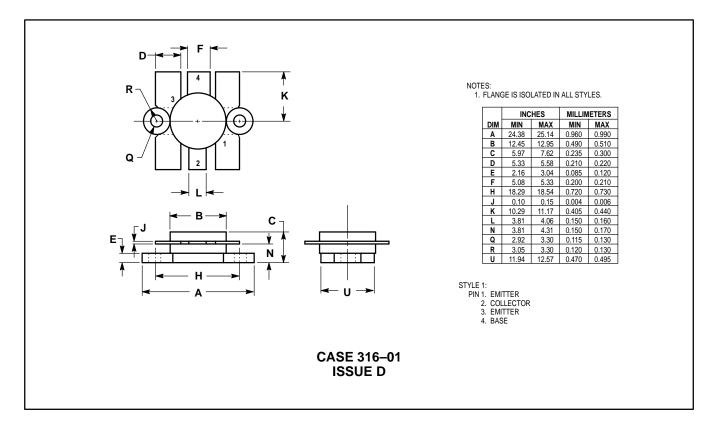
Figure 5. Power Saturation Profile



 $Z_{OL}^*$  = Conjugate of the load impedance into which the device output operates at a given power,  $\eta$ , and frequency.

Figure 6. Series Equivalent Input-Output Impedance

## PACKAGE DIMENSIONS



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